

OSA-1310-CC

SOA Chip On Carrier, 1310nm

OSA-1310-CC is a 1310nm SOA (Semiconductor Optical Amplifier) chip on AIN carrier. It is designed for both high gain and low polarization dependence at a controlled temperature range.

KEY FEATURES

- ✧ High gain in 1310nm LWDM range
- ✧ Low polarization dependent gain
- ✧ Operation at controlled temperature and hermetic package

APPLICATION

- ✧ 100G ZR4 Application
- ✧ Pre-amplifier

DESCRIPTION

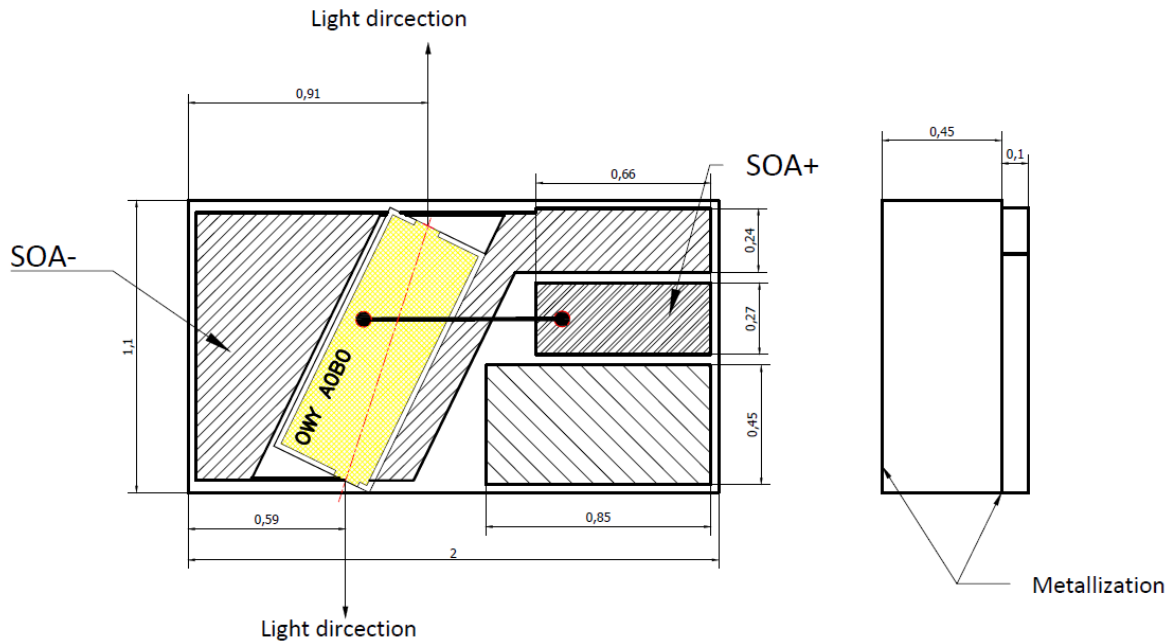
Expected performance not guaranteed. Customer design and assembly process may impact the parameter values.

ELECTRICAL AND OPTICAL CHARACTERISTICS (Test temperature=25°C, unless otherwise specified)						
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
G	Gain	CW, Iop=100mA, Pin=-20dBm*	16	18		dB
PDG	Polarization Dependent Gain	CW, Iop=100mA, Pin=-20dBm*		1	2	dB
Psat	Saturation Power	CW, Iop=100mA, Gain-3dB*	6	7		dBm
NF	Noise Figure	CW, Iop=100mA, Pin=-20dBm*		7.5		dB
P _{ASE}	Optical Power	CW, Iop=100mA		1		mW
V _f	Forward Voltage	CW, Iop=100mA		1.1	1.3	V
F _v	Far-field Angle, Vertical			31		deg
F _h	Far-field Angle, Horizontal			23		deg

*Wavelength of Pin is within LWDM4 channels: 1295.56/1300.05/1304.58/1309.14nm

ABSOLUTE MAXIMUM RATINGS				
Symbol	Parameter	Min	Max	Unit
V _{RL}	LD Reverse Voltage		2	V
I _f	LD Forward Current		200	mA
ESD	ESD(HBD)	500		V
T _{stg}	Storage Temperature	-40	85	°C

MECHANICAL DIMENSION (mm) and PIN ASSIGNMENT



DEVICE HANDLING

- ✧ The chip is sensitive and should be handled with care. Both waveguide section and cavity facets should not be touched to avoid any damage.
- ✧ Electrostatic discharge may cause direct or latent damage to chip. During assembly, precautions for handling electrostatically sensitive devices must be observed.

REVISION HISTORY

Version	Subject	Release Date
1.0	Initial Release	2023/6/1
